IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A manufacturing method of a semiconductor integrated circuit device, comprising the steps of:

(a) depositing a positive type photoresist film over a semiconductor substrate;

(b) exposing a first mask pattern on said positive type photoresist film;

(c) exposing a second mask pattern on said positive type photoresist film so as to be superposed on said first mask pattern;

(d) performing development treatment relative to said positive type resist film after said steps (b) and (c) and thereby forming a photoresist pattern comprising a positive type photoresist pattern on said semiconductor substrate; and

(e) performing etching treatment relative to said semiconductor substrate by using said photoresist pattern as a mask and thereby transferring a transferred pattern on said semiconductor substrate,

wherein said first mask pattern has a pattern for transferring a line pattern; and

wherein said second mask pattern has a plurality of unit cells arranged regularly; and

wherein said second mask pattern has:

a plurality of main light transferring patterns for separating said line pattern;

a plurality of auxiliary light transferring patterns disposed such that a distance between each of said main light transferring patterns and each of said auxiliary light transferring patterns becomes the same in a periphery thereof, and formed at such a

dimension as not to be transferred on said positive type photoresist film; and

a phase shifter disposed in any one of said main light transferring patterns and said auxiliary light transferring patterns and generating a phase difference in a transferring light.

2. (New) The manufacturing method of a semiconductor integrated circuit device according to claim 1, wherein said first mask pattern is a pattern for transferring a gate pattern, and wherein said second mask pattern is a pattern for removing an unnecessary portion transferred on said positive type photoresist film at the time of transfer using said first mask pattern.

3. (New) The manufacturing method of a semiconductor integrated circuit device according to claim 2, wherein said gate pattern is a gate pattern in an SRAM memory cell.